

2N7002PS,115 Datasheet





https://www.DiGi-Electronics.com

DiGi Electronics Part Number 2N7002PS,115-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number 2N7002PS,115

Description MOSFET 2N-CH 60V 0.32A 6TSSOP

Detailed Description Mosfet Array 60V 320mA 420mW Surface Mount 6-T

SSOP



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

ufacturer Product Number:	Manufacture
uracturer Product Number.	Manufacturer:
002PS,115	Nexperia USA Inc.
es:	Product Status:
	Not For New Designs
nnology:	Configuration:
FET (Metal Oxide)	2 N-Channel (Dual)
Feature:	Drain to Source Voltage (Vdss):
c Level Gate	60V
ent - Continuous Drain (Id) @ 25°C:	Rds On (Max) @ Id, Vgs:
mA	1.60hm @ 500mA, 10V
(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
′ @ 250μA	0.8nC @ 4.5V
ıt Capacitance (Ciss) (Max) @ Vds:	Power - Max:
F @ 10V	420mW
rating Temperature:	Grade:
^Р С (ТJ)	Automotive
lification:	Mounting Type:
-Q100	Surface Mount
kage / Case:	Supplier Device Package:
SOP, SC-88, SOT-363	6-TSSOP
Product Number:	
002	

Environmental & Export classification

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



2N7002PS

60 V, 320 mA dual N-channel Trench MOSFET

Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Logic-level compatible
- · Very fast switching
- · Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	er transistor							
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	-	60	V	
V_{GS}	gate-source voltage			-20	-	20	V	
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	320	mA	
Static characte	Static characteristics (per transistor)							
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 500 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.01; T_{j} = 25 °C		-	1	1.6	Ω	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



60 V, 320 mA dual N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	□6 □5 □4	D ₁ D ₂
2	G1	gate1		
3	D2	drain2	0	(未
4	S2	source2	H ₁ H ₂ H ₃	T+15 T+15
5	G2	gate2	TSSOP6 (SOT363)	$\begin{bmatrix} & & & & & & \\ & & & & & & \\ & & & & & $
6	D1	drain1		31 G1 G2 G2 msd901

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
2N7002PS	TSSOP6	plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
2N7002PS	M8 %

[1] % = placeholder for manufacturing site code

60 V, 320 mA dual N-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or		'			
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	320	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	240	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	1.2	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	280	mW
			[1]	-	320	mW
		T _{sp} = 25 °C		-	990	mW
Per device			'			
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	420	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode		'	1		
I _S	source current	T _{amb} = 25 °C	[1]	-	320	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

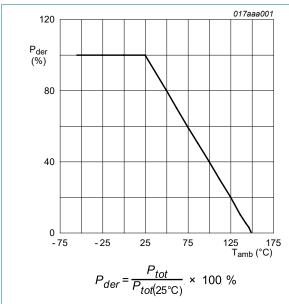


Fig. 1. Normalized total power dissipation as a function of ambient temperature

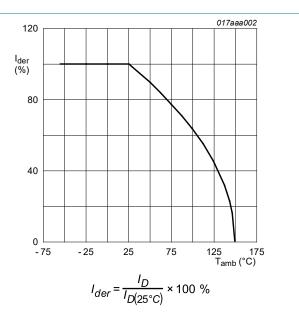
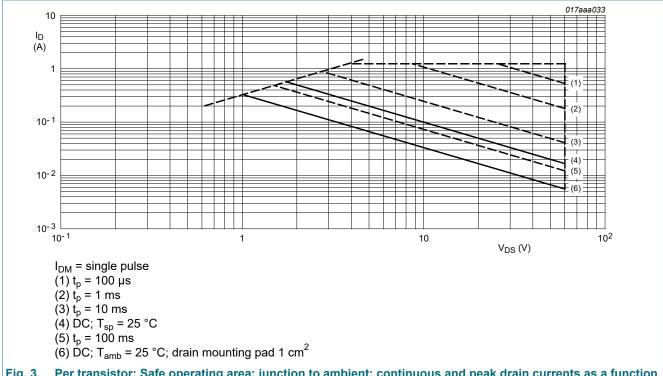


Fig. 2. Normalized continuous drain current as a function of ambient temperature

60 V, 320 mA dual N-channel Trench MOSFET



60 V, 320 mA dual N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device	<u>'</u>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	300	K/W
Per transist	tor						
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	390	445	K/W
	junction to ambient		[2]	-	340	390	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	130	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

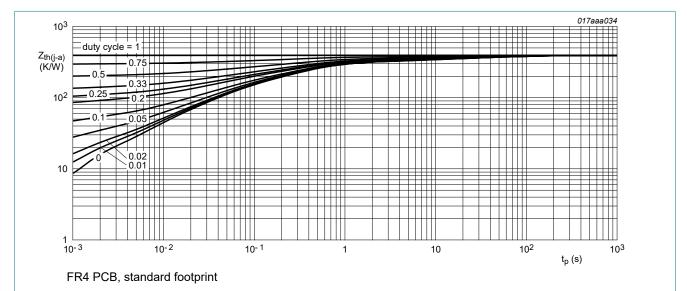


Fig. 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

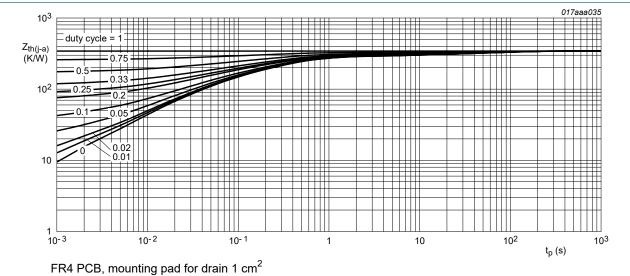


Fig. 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, 320 mA dual N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 10 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.75	2.4	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
DOON	drain-source on-state resistance	V_{GS} = 5 V; I_{D} = 50 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.01; T_{j} = 25 °C	-	1.3	2	Ω
		V_{GS} = 10 V; I_{D} = 500 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.01; T_{j} = 25 °C	-	1	1.6	Ω
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 200 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.01; T_{j} = 25 °C	-	400	-	mS
Dynamic ch	naracteristics (per transist	or)	'	'		
Q _{G(tot)}	total gate charge	$V_{DS} = 30 \text{ V}; I_{D} = 300 \text{ mA}; V_{GS} = 4.5 \text{ V};$	-	0.6	0.8	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.2	-	nC
Q_{GD}	gate-drain charge		-	0.2	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	30	50	pF
C _{oss}	output capacitance	T _j = 25 °C	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 250 \Omega; V_{GS} = 10 \text{ V};$	-	3	6	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4	-	ns
t _{d(off)}	turn-off delay time		-	10	20	ns
t _f	fall time		-	5	-	ns
Source-drai	in diode (per transistor)					
V_{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V; T _i = 25 °C	0.47	0.75	1.1	V

60 V, 320 mA dual N-channel Trench MOSFET

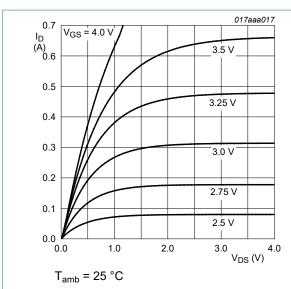
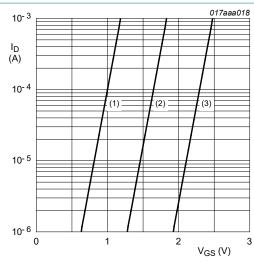


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

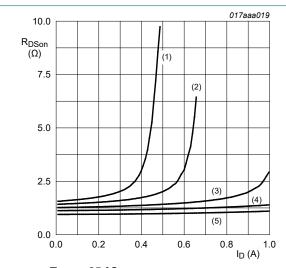


 T_{amb} = 25 °C; V_{DS} = 5 V (1) minimum values

(2) typical values

(3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



 T_{amb} = 25 °C

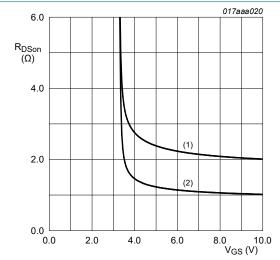
(1) $V_{GS} = 3.25 \text{ V}$

 $(2) V_{GS} = 3.5 V$

(3) $V_{GS} = 4 V$ (4) $V_{GS} = 5 V$

 $(5) V_{GS} = 10 V$





 $I_D = 500 \text{ mA}$

(1) T_{amb} = 150 °C

 $(2) T_{amb} = 25 °C$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

60 V, 320 mA dual N-channel Trench MOSFET

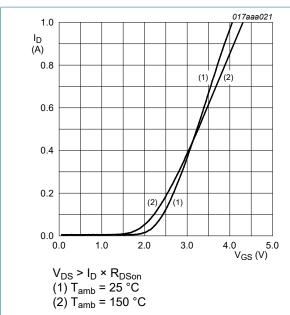


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

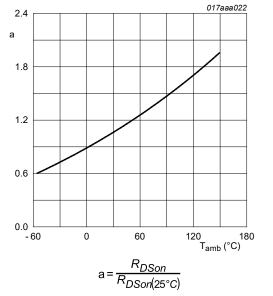
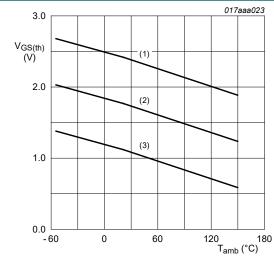


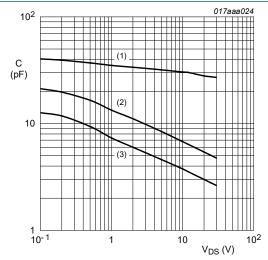
Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of ambient temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

60 V, 320 mA dual N-channel Trench MOSFET

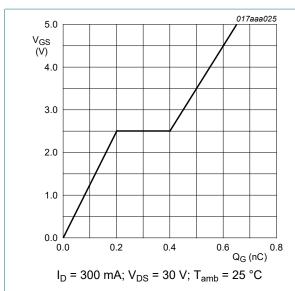


Fig. 14. Gate-source voltage as a function of gate charge; typical values

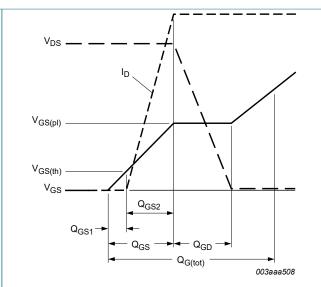
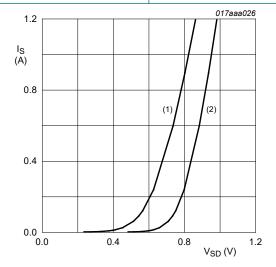


Fig. 15. Gate charge waveform definitions

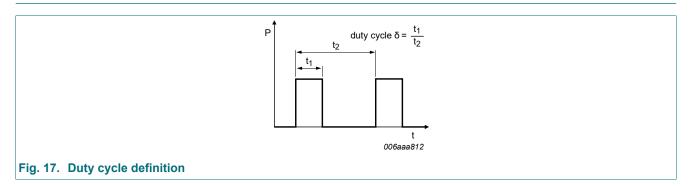


V_{GS} = 0 V (1) T_{amb} = 150 °C (2) T_{amb} = 25 °C

Fig. 16. Source current as a function of source-drain voltage; typical values

60 V, 320 mA dual N-channel Trench MOSFET

11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

60 V, 320 mA dual N-channel Trench MOSFET

12. Package outline

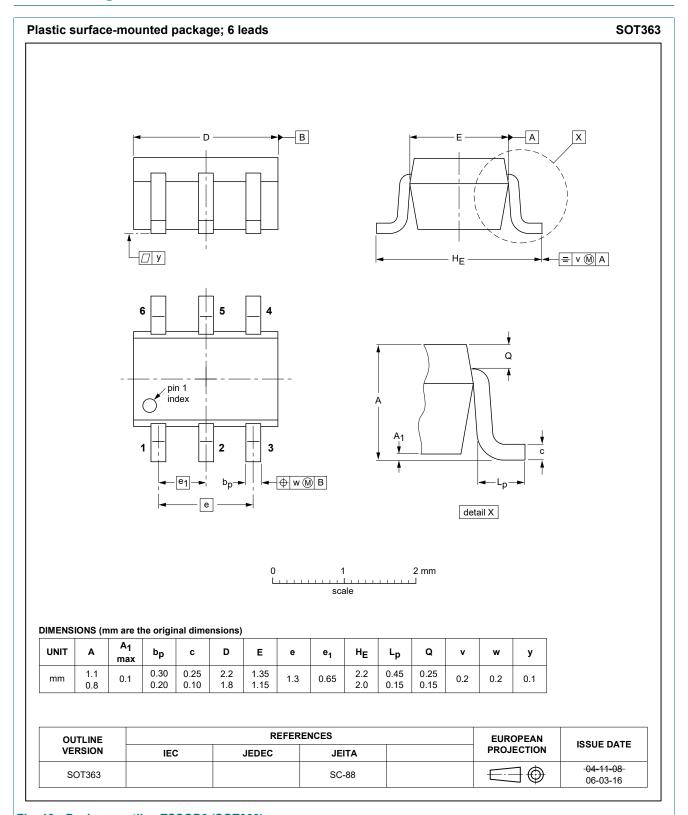
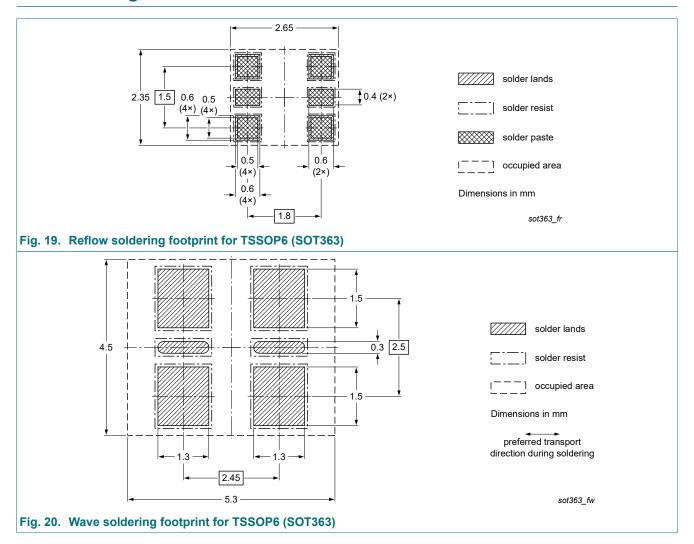


Fig. 18. Package outline TSSOP6 (SOT363)

60 V, 320 mA dual N-channel Trench MOSFET

13. Soldering



60 V, 320 mA dual N-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
2N7002PS v.2	20201123	Product data sheet	-	2N7002PS v.1		
Modifications:	Nexperia. • Legal texts have bee	data sheet has been redesigned to comply with the identity guidelines of been adapted to the new company name where appropriate. eristics": Typo correction for I _{GSS} and switching times.				
2N7002PS v.1	20100701	Product data sheet	-	-		

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at https://www.nexperia.com.

Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Nexperia and its customer, unless Nexperia and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Nexperia product is deemed to offer functions and qualities beyond those described in the Product data sheet.

Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. Nexperia takes no responsibility for the content in this document if provided by an information source outside of Nexperia.

In no event shall Nexperia be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Nexperia's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the Terms and conditions of commercial sale of Nexperia.

Right to make changes — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use in automotive applications — This Nexperia product has been qualified for use in automotive applications. Unless otherwise agreed in writing, the product is not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or

60 V, 320 mA dual N-channel Trench MOSFET

equipment, nor in applications where failure or malfunction of an Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Nexperia and its suppliers accept no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own rick.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Nexperia products, and Nexperia accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Nexperia product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Nexperia does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Nexperia products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Nexperia does not accept any liability in this respect

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — Nexperia products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nexperia.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Nexperia hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Nexperia products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

60 V, 320 mA dual N-channel Trench MOSFET

Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	5
10	. Characteristics	6
11.	. Test information	10
12	. Package outline	11
	. Soldering	
	. Revision history	
	Legal information	

For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 23 November 2020

[©] Nexperia B.V. 2020. All rights reserved



OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we striciy control the quality of products and services. Welcome your RFQ to Email: Info@DiGi-Electronics.com

















Tel: +00 852-30501935